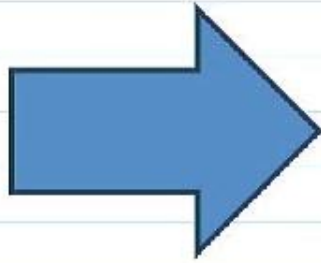
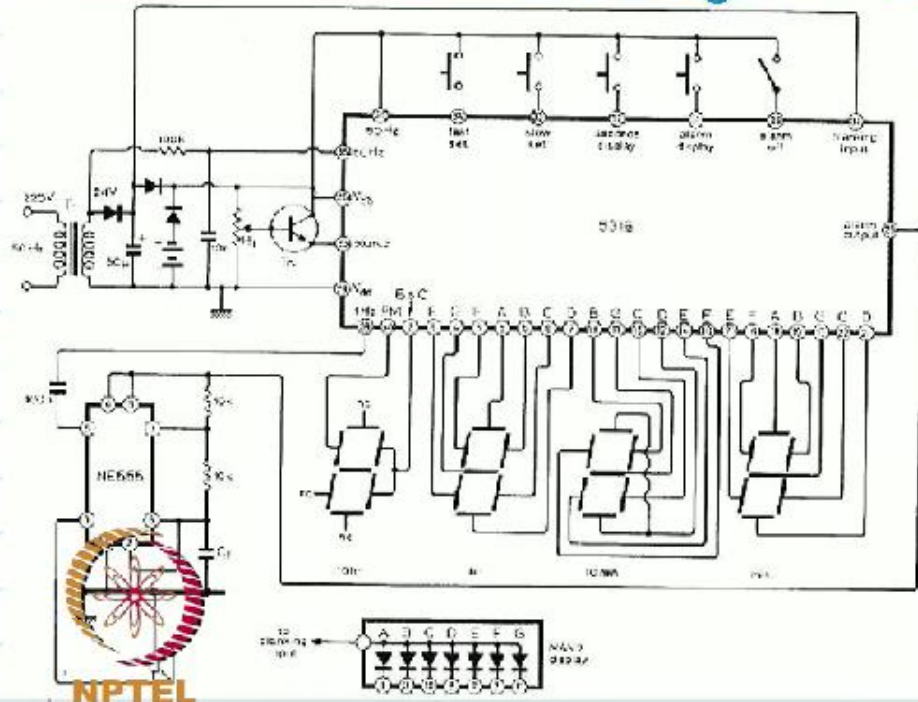


## Electronic System Design :

A circuit can have multiple types of components:

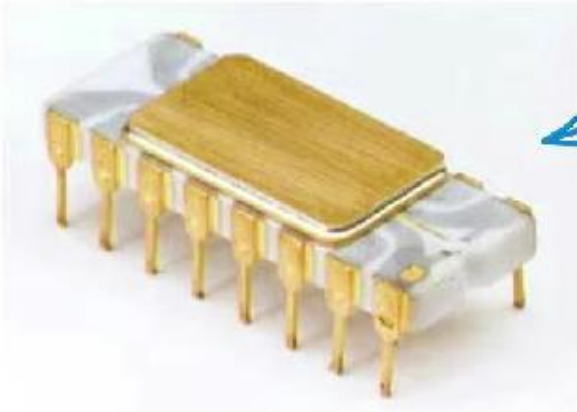
- 1) R, L and C
- 2) Diodes, Transistors
- 3) Integrated Circuits
- 4) Displays, Buttons etc.

## Electronic System Schematic

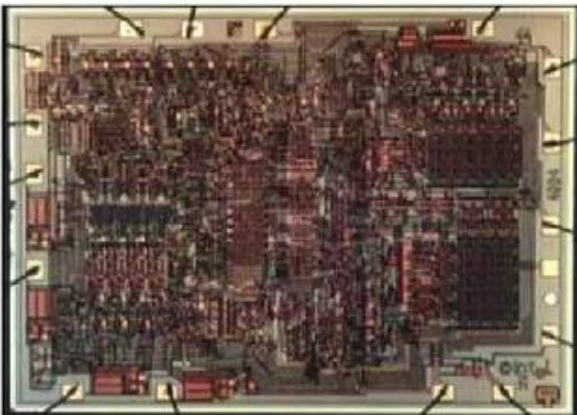


# Intel's 4004 Microprocessor!

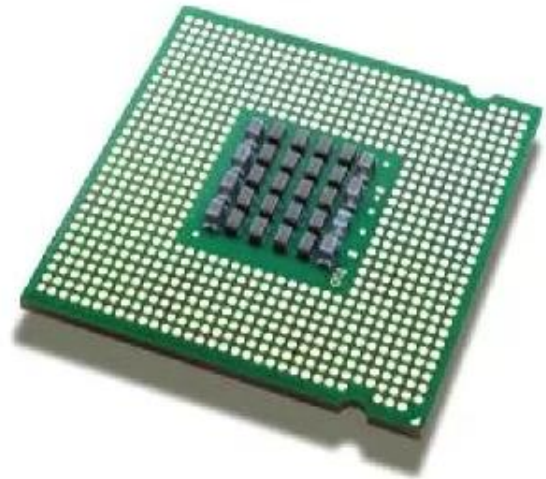
Many transistors connected together.



Packaged  
Microprocessor



4004  $\mu$ processor  
Die - photograph

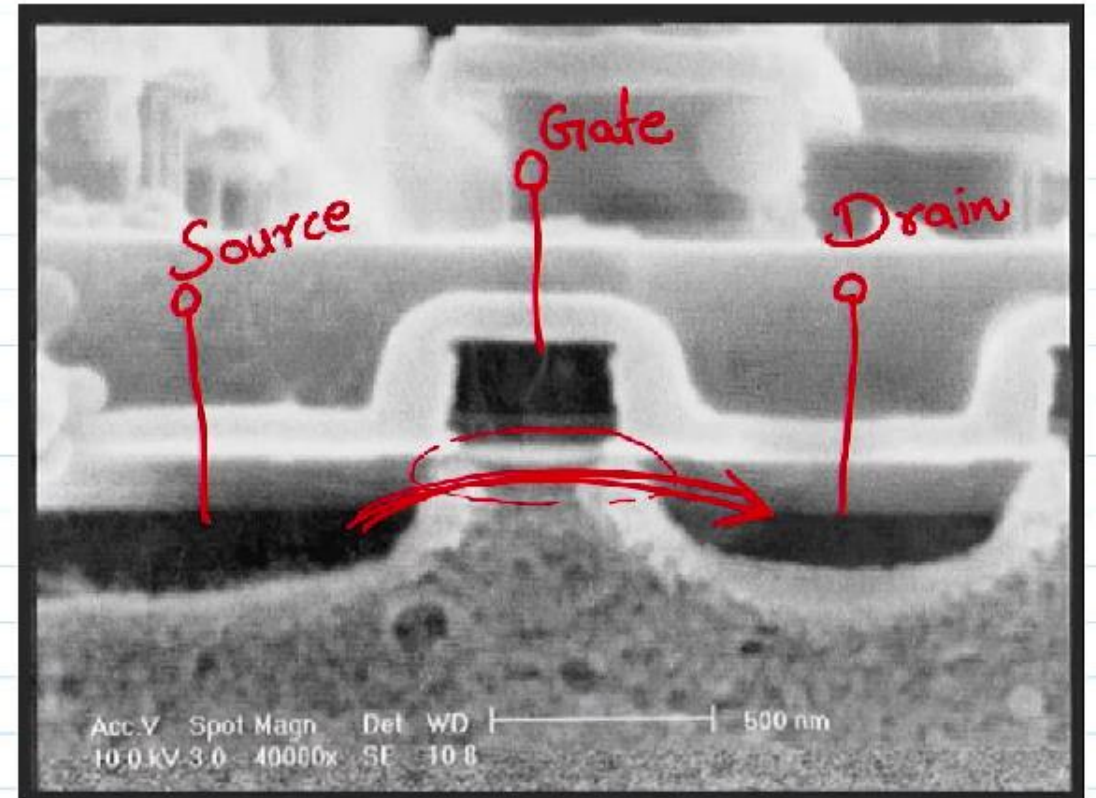
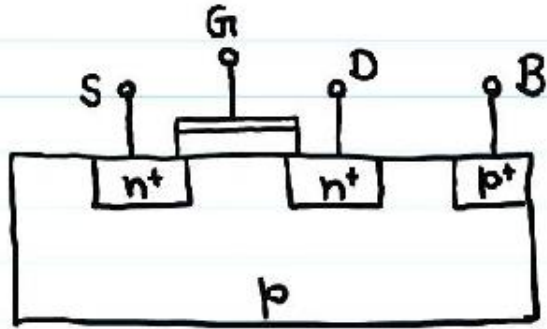




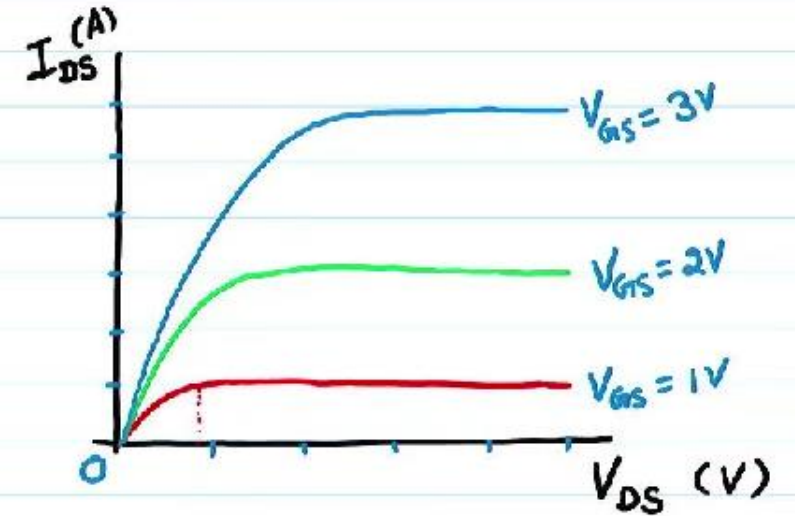
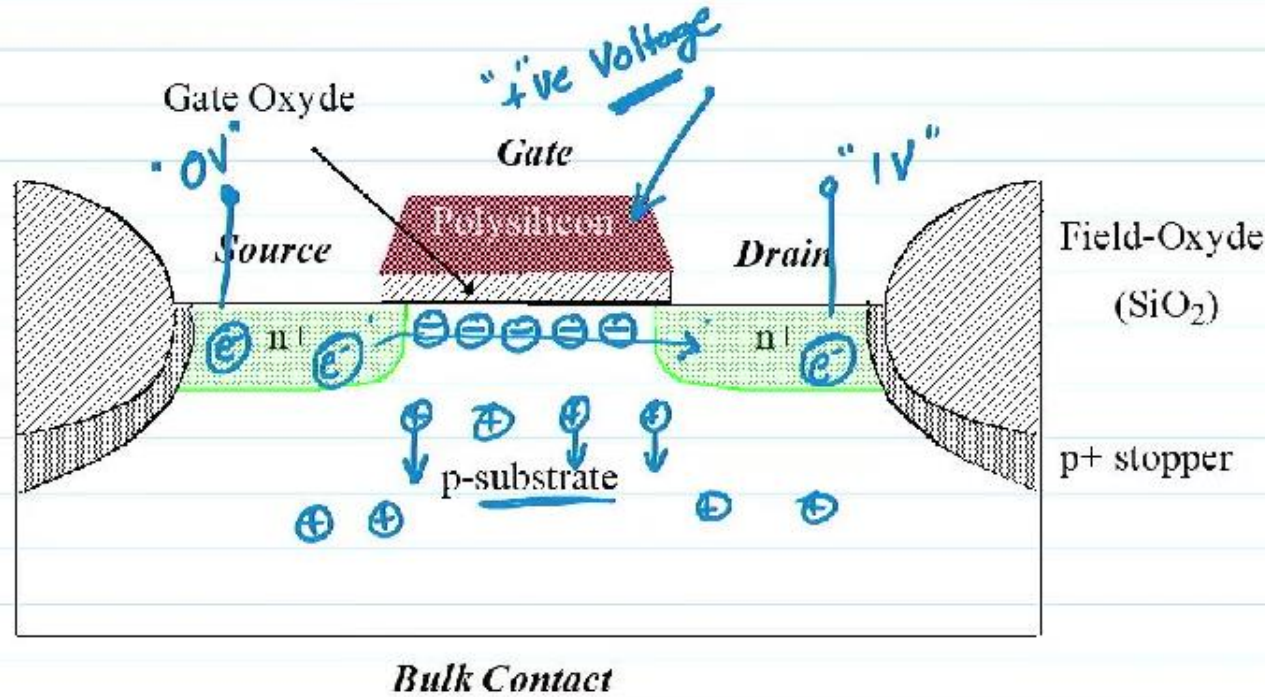
# MOSFET : Metal Oxide Semiconductor Field Effect Transistor

- 1) MOSFETs are most commonly used Field - Effect Transistor.
- 2) Mosfets are used in switching and amplifying signals.
- 3) Mosfets are voltage controlled devices.
- 4) Mosfets are 4 - Terminal devices.
- 5) Mosfets have very high switching speed.
- 6) There are two classes of Mosfets
  - a) Enhancement type.
  - b) Depletion type.
- 7) There are two classes further
  - a) N - channel
  - b) P - channel.

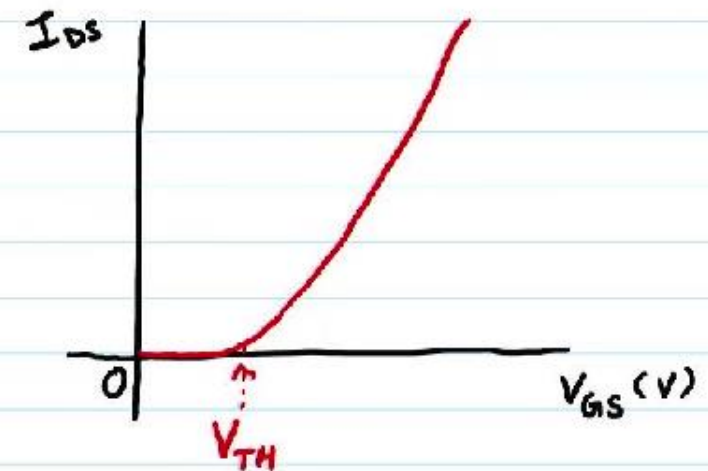
# MOSFET Cross - Section :



# MOSFET Working :



$I_D - V_{DS}$

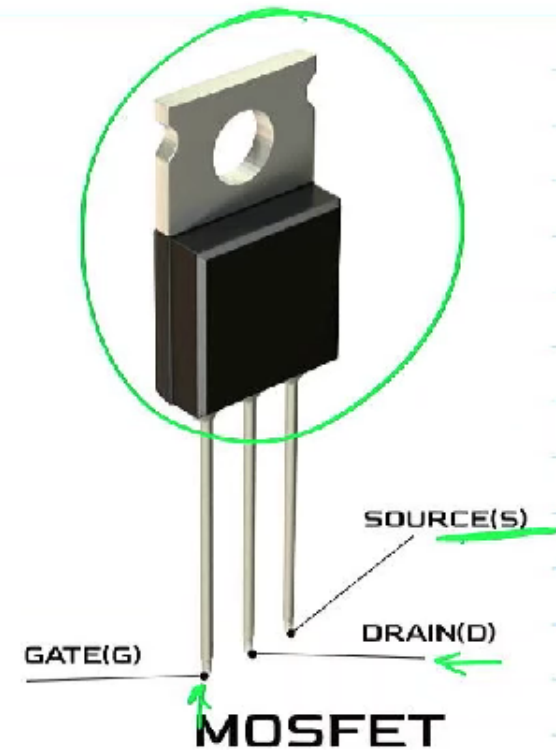
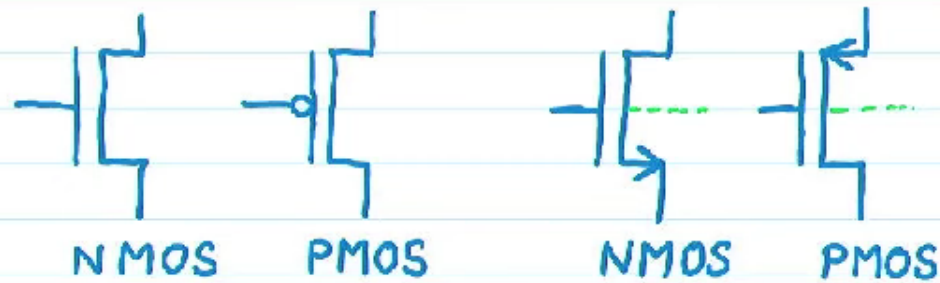


CROSS-SECTION of NMOS Transistor  
at zero-bias  $\rightarrow$  No current ( $I_{DS}$ )

## MOSFET Equations and Symbols:

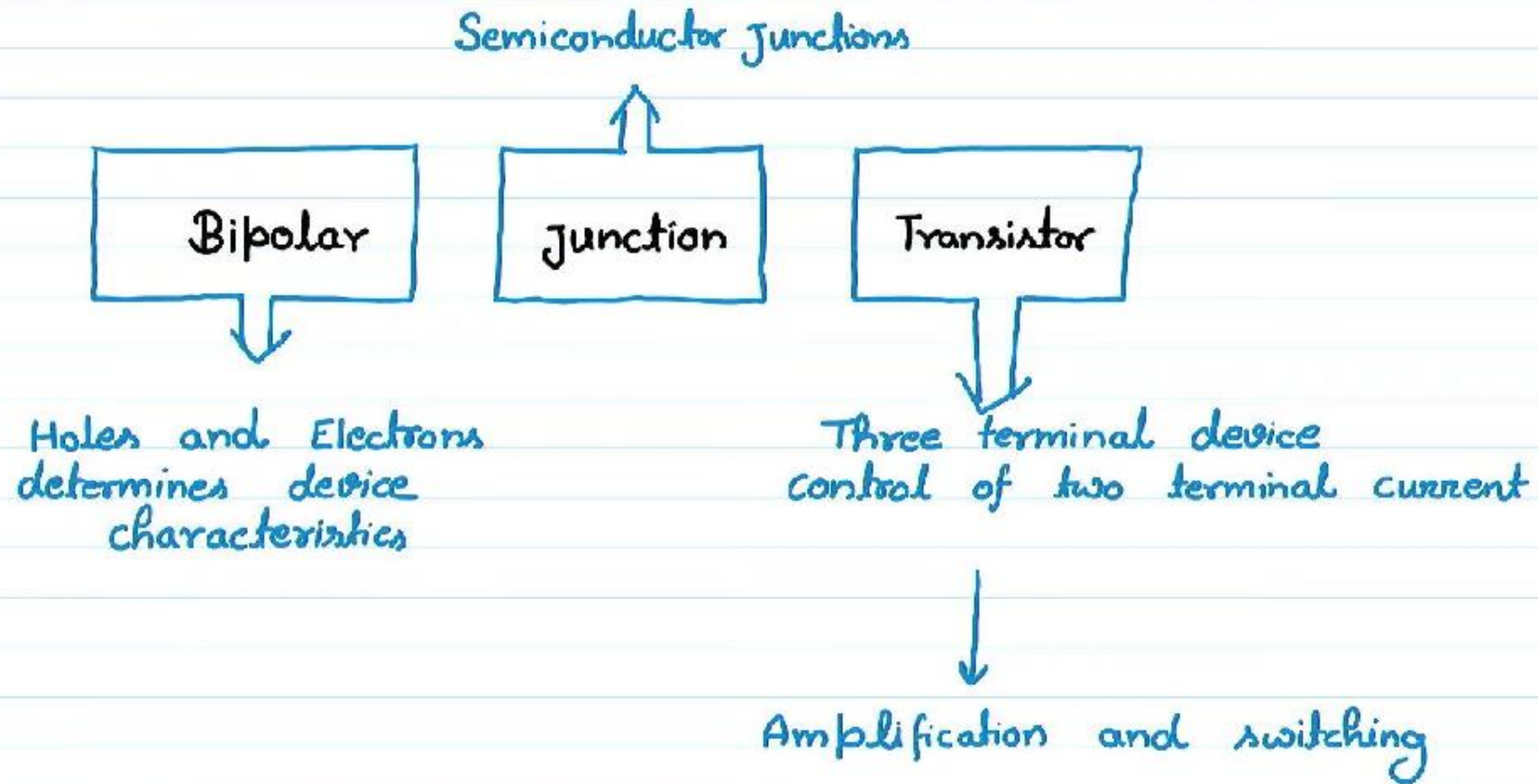
$$I_D = \frac{1}{2} \mu_n C_{ox} \frac{W}{L} (V_{GS} - V_{TH})^2$$

$$g_m = \frac{\partial I_D}{\partial V_{GS}} = \mu_n C_{ox} \frac{W}{L} (V_{GS} - V_T)$$





BJT:

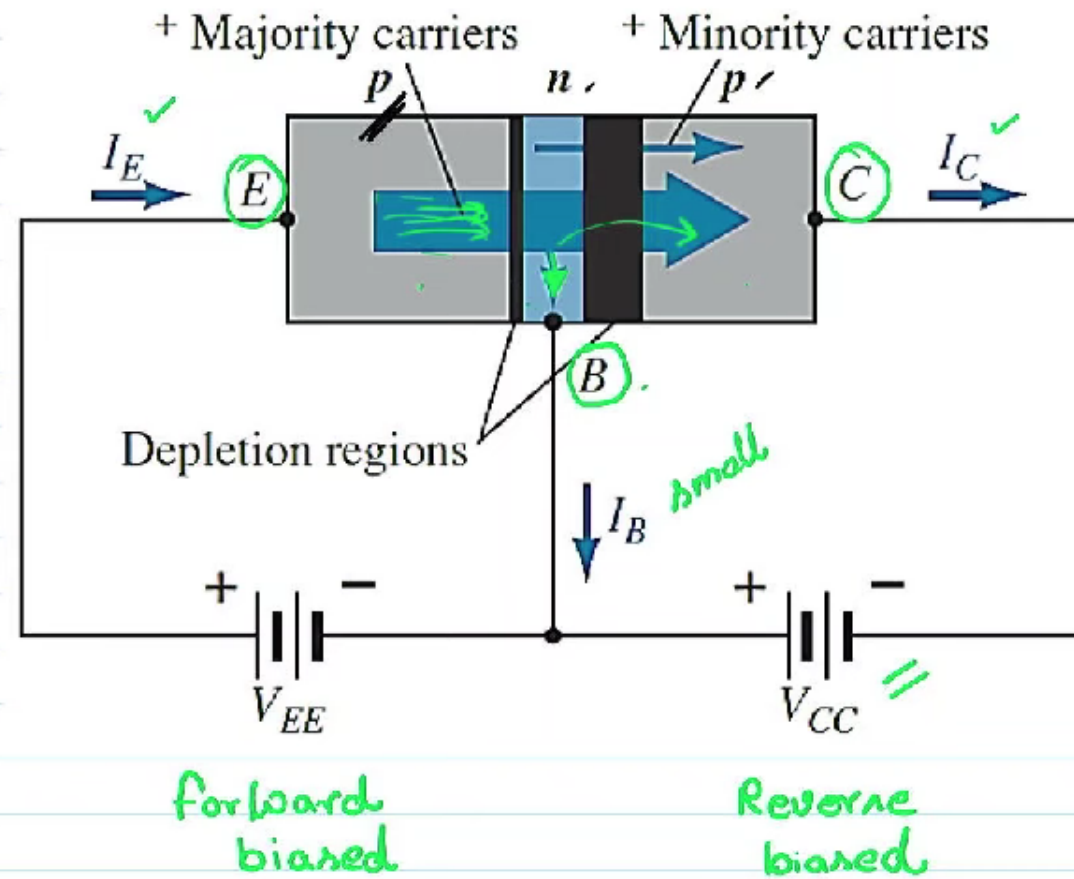


## Bipolar Junction Transistor :

- A N-type silicon sandwiched between two p-type silicon.
- Types of Transistor
  - npn
  - p-n-p
- Three regions of transistor
  - Base
  - Emitter
  - Collector
- Bipolar : Both  $e^-$  and  $h^+$  contribute to current flow.



## BJT Operation :



- E-B junction is forward biased
- C-B junction is reverse biased
- Base is very thin and lightly doped
- base current is very small.

$$I_E = I_C + I_B$$

BJT : Commercially available packages :

